## Pch+Pch -30V 200mA Small Signal MOSFET

| $V_{DSS}$                  | -30V   |
|----------------------------|--------|
| R <sub>DS(on)</sub> (Max.) | 1.4Ω   |
| I <sub>D</sub>             | ±200mA |
| $P_D$                      | 150mW  |

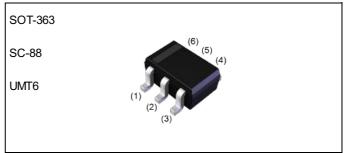
### Features

- 1) Two RSU002P03 transistors in a single UMT package.
- 2) The MOSFET elements are independent, eliminating mutual interference.
- 3) Mounting cost and area can be cut in half.

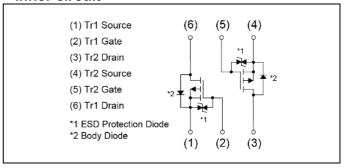
### Application

Switching

### Outline



### •Inner circuit



Packaging specifications

|      | ing opcomoducino          |                  |
|------|---------------------------|------------------|
|      | Packing                   | Embossed<br>Tape |
|      | Reel size (mm)            | 180              |
| Туре | Tape width (mm)           | 8                |
|      | Basic ordering unit (pcs) | 3000             |
|      | Taping code               | TR               |
|      | Marking                   | J01              |

### ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified) < Tr1 and Tr2>

| Parameter                         | Symbol             | Value               | Unit |    |  |
|-----------------------------------|--------------------|---------------------|------|----|--|
| Drain - Source voltage            | V <sub>DSS</sub>   | -30                 | V    |    |  |
| Continuous drain current          | I <sub>D</sub>     | ±200                | mA   |    |  |
| Pulsed drain current              | I <sub>DP</sub> *1 | ±400                | mA   |    |  |
| Gate - Source voltage             | $V_{GSS}$          | ±20                 | V    |    |  |
| Davis and distribution            | total              | D *2                | 150  | mW |  |
| Power dissipation                 | element            | - P <sub>D</sub> *2 | 120  |    |  |
| Junction temperature              | T <sub>j</sub>     | 150                 | °C   |    |  |
| Operating junction and storage te | T <sub>stg</sub>   | -55 to +150         | °C   |    |  |

### ●Thermal resistance

| Parameter                              |         | Symbol               | Values |      |      | 1.1  |
|--|---------|----------------------|--------|------|------|------|
|  |         |                      | Min.   | Тур. | Max. | Unit |
|  | total   | R <sub>thJA</sub> *2 | -      | -    | 833  | °C/W |
| Thermal resistance, junction - ambient | element |                      | 1      | -    | 1042 |      |

## ● Electrical characteristics (T<sub>a</sub> = 25°C) < Tr1 and Tr2>

| Devenuente                                     | Cymah al                                 | Conditions                                      | Values |       |      | l limit |  |
|--|--|---|--------|-------|------|---------|--|
| Parameter Syr                                  |  | ymbol Conditions                                |        | Тур.  | Max. | Unit    |  |
| Drain - Source breakdown voltage               | V <sub>(BR)DSS</sub>                     | V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA     |        | -     | -    | V       |  |
| Breakdown voltage temperature coefficient      | $\frac{\DeltaV_{(BR)DSS}}{\DeltaT_j}$    | I <sub>D</sub> = -1mA<br>referenced to 25°C     | -      | -20.7 | -    | mV/°C   |  |
| Zero gate voltage<br>drain current             | I <sub>DSS</sub>                         | V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V    | -      | -     | -1   | μA      |  |
| Gate - Source<br>leakage current               | I <sub>GSS</sub>                         | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V    |        | -     | ±10  | μA      |  |
| Gate threshold voltage                         | V <sub>GS(th)</sub>                      | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA   |        | -     | -2.5 | V       |  |
| Gate threshold voltage temperature coefficient | $\frac{\Delta V_{GS(th)}}{\Delta T_{j}}$ |   |        | 3.1   | ı    | mV/°C   |  |
|  |  | $V_{GS} = -10V, I_D = -200mA$                   | 1      | 0.9   | 1.4  |         |  |
| Static drain - source<br>on - state resistance | R <sub>DS(on)</sub> *3                   | $V_{GS} = -4.5V, I_D = -150mA$                  | 1      | 1.4   | 2.1  | Ω       |  |
|  |  | $V_{GS} = -4V, I_D = -150mA$                    | -      | 1.6   | 2.4  |         |  |
| Forward Transfer<br>Admittance                 | Y <sub>fs</sub>  *3                      | V <sub>DS</sub> = -10V, I <sub>D</sub> = -150mA | 200    | -     | -    | mS      |  |

## ● Electrical characteristics (T<sub>a</sub> = 25°C) < Tr1 and Tr2>

| Davamatav   | Cumbal                | Conditions                                    | Values |      |      | Unit |  |
|---|-----------------------|---|--------|------|------|------|--|
| Parameter   | Symbol Conditions     |   | Min.   | Тур. | Max. | Uill |  |
| Input capacitance   | C <sub>iss</sub>      | V <sub>GS</sub> = 0V                          | -      | 30   | -    |      |  |
| Output capacitance  | C <sub>oss</sub>      | V <sub>DS</sub> = -10V                        | -      | 4    | -    | pF   |  |
| Reverse transfer capacitance C <sub>rss</sub>             |                       | f = 1MHz                                      | -      | 5    | -    |      |  |
| Turn - on delay time                                      | t <sub>d(on)</sub> *3 | V <sub>DD</sub> ≈ -15V,V <sub>GS</sub> = -10V | -      | 8    | -    |      |  |
| Rise time   | t <sub>r</sub> *3     | I <sub>D</sub> = -150mA                       | -      | 5    | -    |      |  |
| Turn - off delay time ${\mathsf t_{\mathsf d(off)}}^{*3}$ |                       | $R_L = 100\Omega$                             | -      | 30   | -    | ns   |  |
| Fall time   | t <sub>f</sub> *3     | $R_G = 10\Omega$                              | -      | 40   | -    |      |  |

## ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

### <Tr1 and Tr2>

| Downston                   | Cy made ad         | Conditions                                    | Values |      |      | l limit |
|----------------------------|--------------------|---|--------|------|------|---------|
| Parameter                  | Symbol Conditions  |   | Min.   | Тур. | Max. | Unit    |
| Continuous forward current | I <sub>S</sub>     | T - 25°0                                      | -      | -    | 100  | ^       |
| Pulse forward current      | I <sub>SP</sub> *1 | T <sub>a</sub> = 25℃                          | -      | -    | 400  | mA      |
| Forward voltage            | V <sub>SD</sub> *3 | V <sub>GS</sub> = 0V, I <sub>S</sub> = -100mA | -      | -    | -1.2 | V       |

<sup>\*1</sup> Pw≦10µs , Duty cycle≦1%

<sup>\*2</sup> Each terminal mounted on a reference land.

<sup>\*3</sup> Pulsed

### Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

120

100

80

60

40

20

0 50 100 150 200

Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Drain Current Derating Curve

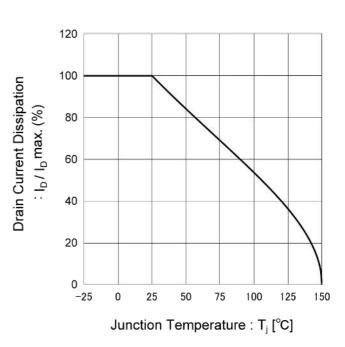


Fig.3 Typical Output Characteristics(I)

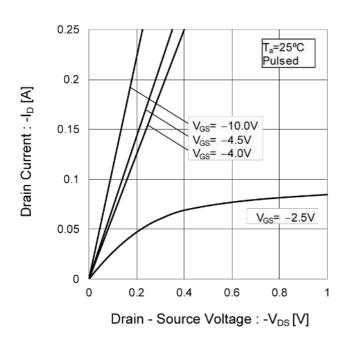
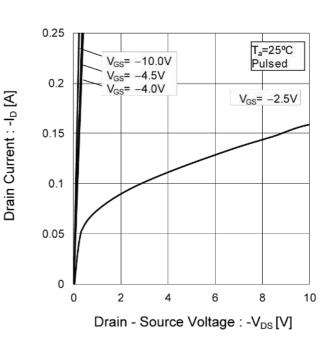


Fig.4 Typical Output Characteristics(II)



### • Electrical characteristic curves

Fig.5 Breakdown Voltage vs.
Junction Temperature

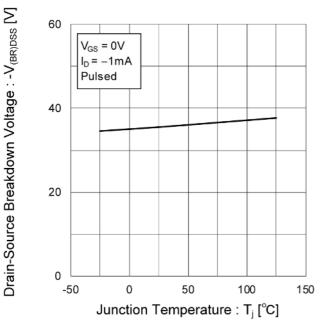


Fig.6 Typical Transfer Characteristics

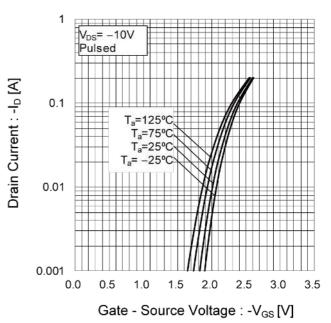


Fig.7 Gate Threshold Voltage vs.
Junction Temperature

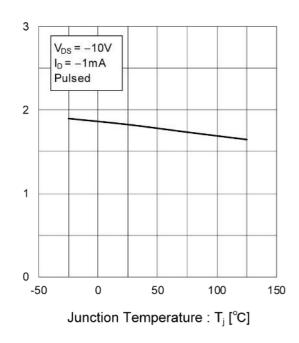
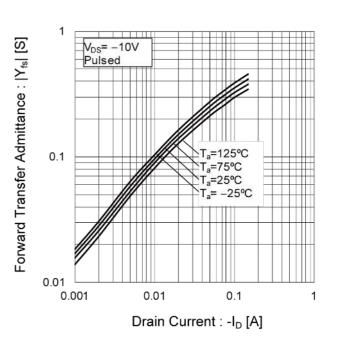


Fig.8 Forward Transfer Admittance vs.
Drain Current



Gate Threshold Voltage: -V<sub>GS(th)</sub> [V]

### • Electrical characteristic curves

Fig.9 Static Drain - Source On - State
Resistance vs. Gate Source Voltage

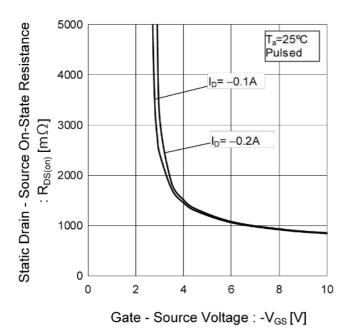


Fig.10 Static Drain - Source On - State
Resistance vs. Junction Temperature

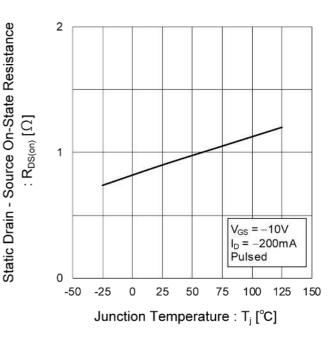
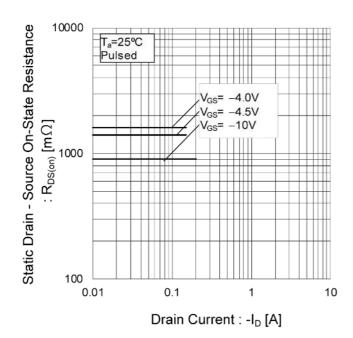


Fig.11 Static Drain - Source On - State
Resistance vs. Drain Current (I)



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### • Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Drain Current (II)

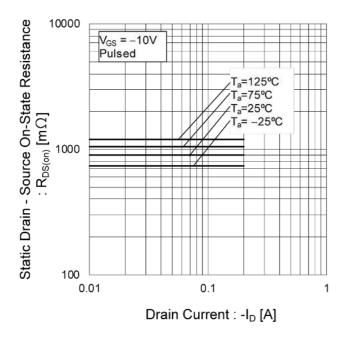


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current (III)

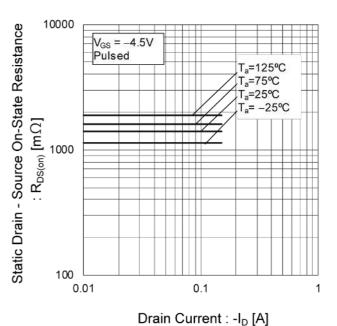
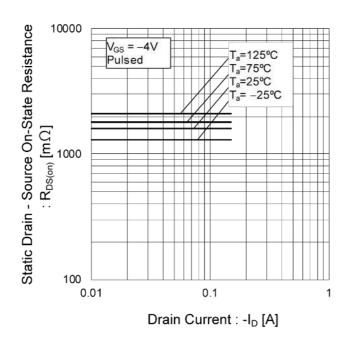


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current (IV)



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### • Electrical characteristic curves

Fig.15 Typical Capacitance vs.

Drain - Source Voltage

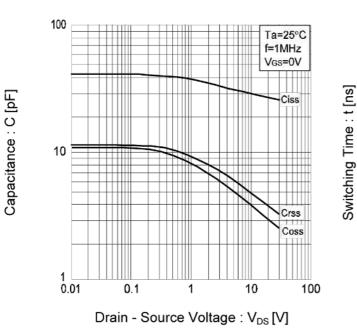


Fig.16 Switching Characteristics

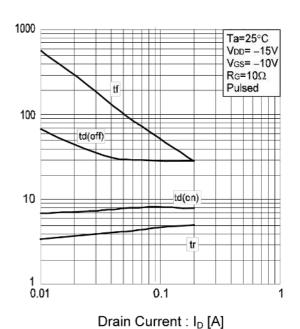
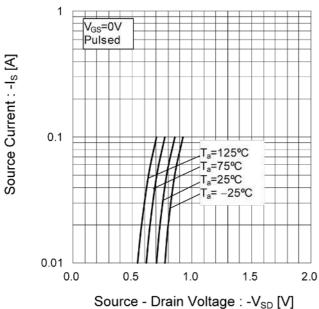


Fig.17 Source Current vs.

Source Drain Voltage



0

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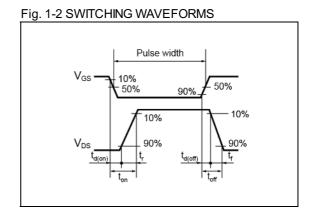
### Measurement circuits

Fig. 1-1 SWITCHING TIME MEASUREMENT CIRCUIT

VGS

D.U.T.

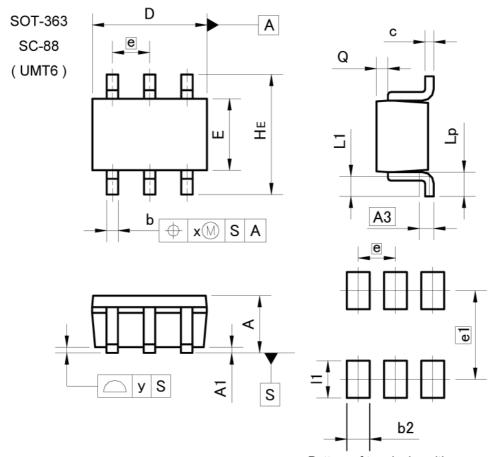
VDD



### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

### Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

| DIM   | MILIM  | ETERS | INC            | HES   |
|-------|--------|-------|----------------|-------|
| DIM - | MIN    | MAX   | MIN            | MAX   |
| Α     | 0.80   | 1.00  | 0.031          | 0.039 |
| A1    | 0.00   | 0.10  | 0.000          | 0.004 |
| A3    | 0.3    | 25    | 0.0            | 10    |
| b     | 0.15   | 0.30  | 0.006          | 0.012 |
| С     | 0.10   | 0.20  | 0.004          | 0.008 |
| D     | 1.90   | 2.10  | 0.075          | 0.083 |
| E     | 1.15   | 1.35  | 0.045          | 0.053 |
| е     | 0.0    | 65    | 0.0            | 26    |
| HE    | 2.00   | 2.20  | 0.079          | 0.087 |
| L1    | 0.10   | 0.40  | 0.004          | 0.016 |
| Lp    | 0.25   | 0.55  | 0.010          | 0.022 |
| Q     | 0.10   | 0.30  | 0.004          | 0.012 |
| х     | -0     | 0.10  | ( <del>-</del> | 0.004 |
| У     | -      | 0.10  | \$ <del></del> | 0.004 |
| DIM   | MILIMI | ETERS | INC            | HES   |
| DIM   | MIN    | MAX   | MIN            | MAX   |
| b2    | -1     | 0.40  | h <del></del>  | 0.016 |
| e1    | 1.5    | 55    | 0.0            | 61    |
| 11    | -2     | 0.65  | 7.00           | 0.026 |

Dimension in mm/inches

Rev.003

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(Note1) Medical Equipment Classification of the Specific Applications

| JAPAN   | USA       | EU         | CHINA     |
|---------|-----------|------------|-----------|
| CLASSⅢ  | CL ACCIII | CLASS II b | CI ACCIII |
| CLASSIV | CLASSⅢ    | CLASSⅢ     | CLASSIII  |

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  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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